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November 28, 2001

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TECHNOLOGY CENTER 2800

TO: Commissioner for Patents
 Atto: Mark V. Prenty
 Patent Examining Corps
 Facsimile Center
 Washington, D.C. 20231

FROM: David C. Peterson

OUR REF: 303.229US2

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* Please deliver to Examiner **Mark V. Prenty** in Art Unit 2822. *

Document(s) Transmitted: An Amendment and Response Under 1.116 (6 pgs.) and a Clean Verison of Pending Claims (4 pgs.)

Total pages of this transmission, including cover letter: 11 pgs

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In re. Patent Application of: Leonard Forbes

Examiner: Mark V. Prenty

Serial No.: 09/132,157

Group Art Unit: 2822

Filed: August 11, 1998

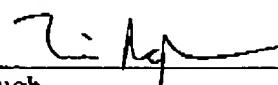
Docket No.: 303.229US2

Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

Please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

By: 
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EXPEDITED PROCEDURE - EXAMINING GROUP 2822

S/N 09/132,157

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes Examiner: Mark V. Prenty
Serial No.: 09/132,157 Group Art Unit: 2822
Filed: August 11, 1998 Docket: 303.229US2
Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION
IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116

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In response to the final Office Action mailed September 25, 2001, please amend the application as follows:

IN THE CLAIMS

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect amendment of previously pending claims 11, 24, 25, 28, 38, 40, and 41. The specific amendments to individual claims are detailed in the following marked up set of claims.

11. (Six times amended) A p-channel metal-oxide-semiconductor transistor, comprising:

 - a silicon substrate;
 - a silicon dioxide (SiO_2) gate oxide, coupled to the substrate;
 - a gate, coupled to the SiO_2 gate oxide;
 - source/drain regions formed in the substrate on opposite sides of the gate; and
 - a $\text{Si}_{1-x}\text{Ge}_x$ channel region, having a germanium molar fraction x, located underneath the SiO_2 gate oxide and between the source/drain regions, wherein x is less than or equal to 0.6, and wherein the $\text{Si}_{1-x}\text{Ge}_x$ channel region forms a continuous $\text{Si}_{1-x}\text{Ge}_x/\text{SiO}_2$ gate oxide interface wherein no germanium oxide is present at the $\text{Si}_{1-x}\text{Ge}_x/\text{SiO}_2$ gate oxide interface as a result of ion implantation of germanium through the previously formed SiO_2 gate oxide.